

/ Descriptions

TO-126F PNP Silicon PNP transistor in a TO-126F Plastic Package.

/ Features

$V_{CE(sat)}$, h_{FE}
Low saturation voltage, excellent h_{FE} linearity and high h_{FE} .

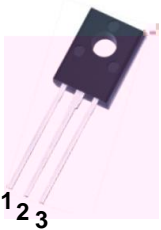
/ Applications

Power amplifier and switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

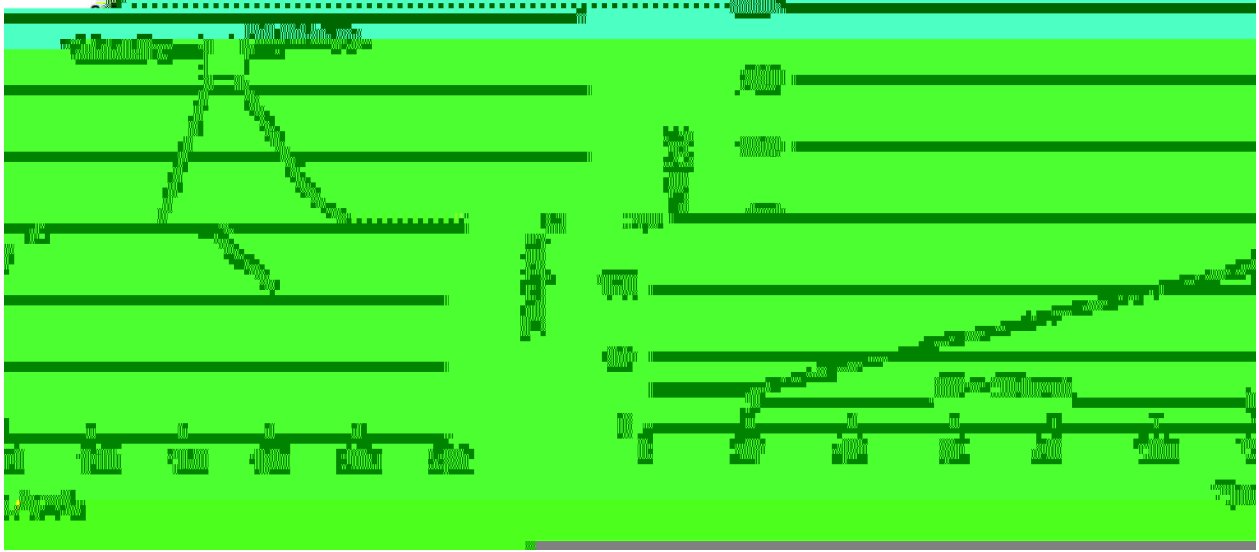
/ h_{FE} Classifications & Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-3.0	A
Peak Collector Current – Continuous	I_{CM}	-7.0	A
Base Current - Continuous	I_B	-0.6	A
Collector Power Dissipation	$P_C (T_C=25^\circ C)$	10	W
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-100\mu A$ $I_E=0$	-50			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-5mA$ $I_B=0$	-50			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-100\mu A$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-50V$ $I_E=0$			-1.0	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-3.0V$ $I_C=0$			-1.0	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-2.0V$ $I_C=-1.0A$	100		400	
	$h_{FE(2)}$	$V_{CE}=-2.0V$ $I_C=-20mA$	100			
Collector to Emitter Saturation Voltage	V					

() / Temperature Profile for Dip Soldering(Pb-Free)



- | | | | | | | |
|---|-------|-----|-----------|--------|---|--------------------------------------|
| 1 | 25 | 150 | 60 | 90sec; | Note: | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | | 2.Peak Temp.:255±5 , Duration:5±0.5sec. | |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. | |

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension (unit mm ³)		

/ TUBE

Package Type	Units					Dimension (unit mm ³)		